

60V, 2.5A Integrated Photo Flash Charger with IGBT Driver and Quench

The Future of Analog IC Technology

DESCRIPTION

The MP3352 is a fast, highly efficient, precision high-voltage photo-flash charger with integrated IGBT driver for xenon flash applications. The programmable peak current is up to 2.5A to ensure fast charging time. A 200m Ω internal power switch minimizes the conduction loss. In addition, a 60V maximum voltage lowers the transformer turns ratio and improves the switching loss associated with the primary leakage inductance. External feedback provides 3% charge accuracy.

The MP3352 is available in a 16-pin 3mm x 3mm QFN package.

FEATURES

- Integrated 60V, 200m Ω Power Switch
- Programmable Peak Current Up to 2.5A
- 3% Charge Accuracy
- <1uA Shutdown Current
- Integrated IGBT Driver
- Integrated Quench Feature

APPLICATIONS

- Digital Still Cameras
- Optical Film Cameras
- Mobile Phones With Camera
- PDAs With Camera

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TYPICAL APPLICATION

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PACKAGE REFERENCE

For Tape & Reel, add suffix –Z (e.g. MP3352DQ–Z)
For RoHS compliant packaging, add suffix –LF (e.g. MP3352DQ–LF–Z)

ABSOLUTE MAXIMUM RATINGS ⁽¹⁾

V _{IN} to GND0.3V to 6V	
CHARGE, ISET, IGBTIN, RDYB, QREF, QSNS	
to GND0.3V to 6V	
FB to GND0.3V to 6V	
SW to GND0.3V to 60V	
Maximum Operating Frequency	
Operating Temperature Ranges: -40°C to +85°C	
Storage Temperature55°C to +150°C	
Junction Temperature+150°C	
Lead Temperature (Solder)+260°C	

Thermal Resistance ⁽²⁾

QFN16 (3mmx3mm)...... 50 12... °C/W

 θ_{JA}

 $\boldsymbol{\theta}_{JC}$

Notes:

1) Exceeding these ratings may damage the device.

2) Measured on approximately 1" square of 1 oz copper.

ELECTRICAL CHARACTERISTICS

(V_{IN}=V (CHARGE)=3.3V, TA = +25°C, unless otherwise noted.)

Parameter	Conditions	Min	Тур	Max	Unit
Photoflash Capacitor Charger					
V _{IN} Voltage Range		3		6	V
V _{IN} UVLO	Rising edge, hysteresis = 200mV	2.7	2.8	2.9	V
V _{IN} Quiescent Current	V(CHARGE)=High, V(SW) = 0, free run by T _{ONMAX}		1	2	mA
V _{IN} Quiescent Current	Charge Complete, V(CHARGE)=High, V(FB) = 1.3V		50		μA
Shutdown Current from V _{IN}	V(CHARGE)=Low			1	μA
V _{SW} Leakage Current	V _{IN} =3.3V,V _{SW} =60V, in Shutdown			2	μA
SW ON resistance between SW and GND	Switch turn-on		0.2		Ω
Charge Input High Voltage		2.4			V
Charge Input Low Voltage				0.6	V
Pull-down resistance of CHARGE pin	V(CHARGE)=3.3V		100K		Ω
I _{PEAK1}	R _{SET} =33.2kΩ	1.36	1.51	1.66	А
I _{PEAK2}	R _{SET} =100kΩ	0.4	0.5	0.6	А
Charge completion detect voltage at FB		1.176	1.20	1.224	V
FB input bias current I(FB)		-0.2		0.2	μA
DCM Comparator threshold	With 1.2K Ω (1%) connected to FB	15	25	35	mV

ELECTRICAL CHARACTERISTICS (continued)

Parameter	Conditions	Min	Тур	Max	Unit
RDYB Leakage Current	V(RDYB)=3.3V			1	μA
RDYB Output Low Voltage	I _{SINK} = 2mA		0.2		V
MAX T _{ON}	Maximum T _{ON} time	45	75	105	μs
Thermal Shutdown	Rising edge, hysteresis = 15°C		150		О°
QREF input current	Q _{REF} =0.2V to 1.2V	-0.1		0.1	μA
QSNS-QREF offset voltage	Q _{REF} =0.2V to 1.2V	-50		50	mV
QSNS input current	Q _{REF} =0.2V to 1.2V	-0.1		0.1	μA
QSNS to IGBT Delay	Q _{REF} =0.2V to 1.2V		2		μs
IGBT Driver					
IGBTOUT pull-up ON			5		Ω
resistance			5		32
IGBTOUT pull-down ON			5		Ω
resistance			5		
IGBTIN Input High Voltage		2.4			V
IGBTIN Input Low Voltage				0.6	V
Propagation delay	IGBTIN rising/falling edge to		45		ns
	IGBTOUT rising/falling edge,				
	C _{GATE} =6500pF				
IGBTOUT rise time	C _{GATE} =6500pF,20% to 80%		60		ns
IGBTOUT fall time	C _{GATE} =6500pF,20% to 80%		70		ns
Pull down resistance of			100K		Ω
IGBTIN					

PIN FUNCTIONS

Pin #	Name	Function
1	ISET	Peak Current Set Input. The peak current is 5X10 ⁴ the current flow out of this pin.
2	GND	Analog Ground. Tie it directly to local ground plane.
3	QREF	Quench reference input.
4	QSNS	Quench sense input from light sensor.
5	IGBTOUT	Output Drive for IGBT Gate. Connect this pin to the gate of the IGBT.
6	VIN	Input Supply Pin. Connect it to system supply voltage. Bypass VIN to GND
		with a 2x10µF or greater ceramic capacitor.
7, 8	PGND	Power Ground. Ground connection for the power switch.
9	CHARGE	Charge Enable Pin. A low-to-high transition on this pin puts the part into power
		delivery mode. Once the target voltage is reached, the part will stop charging
		the output. Toggle this pin will start charging again. Bring this pin low will
		terminate the power delivery and put the part in shutdown.
10, 11	N/C	No Connect
12, 13	SW	Switch Pin. This is the drain of the internal power switch.
14	IGBTIN	Logic Input Pin for IGBT Drive.
15	RDYB	Open-Drain Power-Ready Output. RDYB goes low when the output voltage is
		reached.
16	FB	Feedback Pin. Trip voltage is 1.2V.

TYPICAL PERFORMANCE CHARACTERISTICS

$T_A = +25^{\circ}C$, unless otherwise noted.



Charging Waveform





Switching Waveform



Charging Waveform



400ms/div



200ms/div

TYPICAL PERFORMANCE CHARACTERISTICS (continued)









100µs/div





VOUT VS. VIN





TEST CIRCUITS





APPLICATION INFORMATION

MP3352 controlled flyback charger operates in critical conduction mode with peak current set by ISET pin. Output voltage is divided down through R1, R2 from the positive terminal of the transformer secondary and compares with 1.20V at FB pin. The low to high transition of CHARGE pin will enable the flyback converter to switch.

Charger may enter DCM mode when charge is close to full and actual OFF time is less than minimum TOFF. Circuit will stop switching and RDYB will be pulled low once the flash capacitor is charged to 300V, a value set by R2, R5, and When the part is ready the internal R8. dissipation is reduced to just the circuits for IGBT driver. Toggle CHARGE pin will start charge again. Bringing CHARGE pin low terminates the power delivery and put the part in shutdown. A maximum T_{ON} timer prevents pulling current from starved power source. If the ON time exceeds maximum $T_{\mbox{\scriptsize ON}},$ the switch is forced OFF regardless of IPEAK detection. Integrated IGBT driver uses V_{IN} as its power supply.

DCM Comparator

DCM boundary is reached when V (FB) drops to zero. The DCM comparator compares V (FB) and a fixed offset voltage of 25mV to account for the comparator delay.

Charge Speed

The output capacitor charging speed is determined by:

$$\Gamma_{\text{charge}} \propto \frac{I_{\text{LIM}}}{\frac{1}{V_{\text{IN}}} + \frac{N}{V_{\text{OUT}}}}$$

Setting Peak Charge Current

MP3352's peak charge current (I_{SET}) can be set by an external resistor, R_{SET} from the ISET pin to ground. The value of R_{SET} can be calculated from:

$$\mathsf{R}_{\mathsf{SET}}(\mathsf{K}\Omega) = \frac{50}{\mathsf{I}_{\mathsf{SET}}(\mathsf{A})}$$

For example, for 2.5A peak charge current, R_{SET} is 20k $\Omega.$

Primary Inductance

The primary inductance is calculated based on the minimum off time period:

$$L_{primary} \geq \frac{V_{out}T_{min,off}}{NI_{neak}}$$

 V_{OUT} : output voltage about 300V T_{MIN-OFF} Minimum off time 300ns. I_{PEAK}: primary peak current

Turns Ratio

The minimum turns ratio of the flyback transformer is obtained as:

$$N \!\geq\! \frac{V_{\text{out}}}{V_{\text{ds}}-V_{\text{in}}}$$

 V_{DS} : FET drain-source voltage V_{IN} : Input voltage 3~5V

Part Number	Description	Size (L×W×H)	Vendor
TTRN-038S T-19-060	1:8, Lprimary = 6µH, for I _{LIM} = 2.5 Amax	6.4mm×7.7mm×4.0mm	TOKYO Coil
750310448	1:8, Lprimary = 6µH, for I _{LIM} = 2.5 Amax	7mm×10mm×5mm	Wurth Electronics
LDT565630T-042	1:8, Lprimary = 6µH, for I _{LIM} = 2A only	5.8mm×5.8mm×3mm	TDK

Table 1—Recommended Transformer Table



Setting Output Voltage

The output voltage is set by selecting the resistive voltage divider ratio. If we use $1.2k\Omega$ the low side resistor (R8) of the voltage divider, we can determine the high side resistor (R2, R5) by the equation:

$$R_2 = R_5 = \frac{1}{2} \frac{V_{out} - V_{FB}}{V_{FB}} R_8$$

Typical values are R2=R5=150kΩ and R8=1.2kΩ.

Output Diode Selection

The reverse voltage of the output diode is determined by:

$$V_{\text{D}} = V_{\text{out}} + NV_{\text{in}}$$

TYPICAL APPLICATION CIRCUIT

Quench Function

MP3352 has build-in guench function to accurately control exposure time and preserve power, thus to extend battery life.

When output capacitor is fully charged and IGBTIN (pin14) is set high, internal IGBT driver drives the gate of IGBT high and fires the flash strobe. Once the photo transistor gets the flash light, it starts to charge C and the voltage of C represents the total exposure. IGBT will be off when the voltage on C exceeds the control voltage on QREF (Pin3)



VIN VIN 2 Cell Li-lon Battery 5.4V to 8.4V C1 10µF 1206 16V GND 🗖 VCC VCC 🗖 VIN SW 3.3V to 5V ŝW R4 100kΩ CHARGE CHAG FB R8 1.2kΩ MP3352 Xenon Flash 15 (RDYB RDYB ISET Ş R9 20kΩ QREF QREF IGBTOUT 600 QSNS QSNS IGBTIN R12 20Ω Q1 FGR15N40A PGND GND PGND NC NC R15 20kΩ IGBTIN 10 11 \diamond

Figure 2—Application Circuit for 2 Cell Li-Ion Battery Photo Flash Charger



PACKAGE INFORMATION



RECOMMENDED LAND PATTERN

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